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November 2013

FQB55N10

N-Channel QFET® MOSFET

100 V, 55 A, 26 mΩ

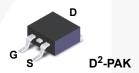
Description

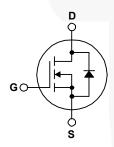
This N-Channel enhancement mode power MOSFET is • 55 A, 100 V, $R_{DS(on)}$ = 26 m Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 75 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 130 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_D = 27.5 A$

- · 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQB55N10TM	Unit
V _{DSS}	Drain-Source Voltage		100	V
I _D	Drain Current - Continuous (T _C = 25°C)		55	А
	- Continuous (T _C = 100°C)		38.9	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	220	Α
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	1100	mJ
I _{AR}	Avalanche Current	(Note 1)	55	Α
E _{AR}	Repetitive Avalanche Energy (Note		15.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		6.0	V/ns
P _D	Power Dissipation (T _A = 25°C) *		3.75	W
	Power Dissipation (T _C = 25°C)		155	W
	- Derate above 25°C		1.03	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
Tı	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C
'L			300	C

Thermal Characteristics

Symbol	Parameter	FQB55N10TM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.97	
D	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQB55N10TM	FQB55N10	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.1		V/°C
I _{DSS}	Zoro Coto Voltago Droin Current	V _{DS} = 100 V, V _{GS} = 0 V			1	μА
	Zero Gate Voltage Drain Current	V _{DS} = 80 V, T _C = 150°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 25 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 27.5 A		0.021	0.026	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 27.5 A		38		S
Dynam	ic Characteristics					
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		2100	2730	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		640	830	pF
C _{rss}	Reverse Transfer Capacitance			130	170	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 50 \text{ V}, I_{D} = 55 \text{ A},$ $R_{G} = 25 \Omega$		25	60	ns
t _r	Turn-On Rise Time			250	510	ns
t _{d(off)}	Turn-Off Delay Time			110	230	ns
t _f	Turn-Off Fall Time	(Note 4)		140	290	ns
Qg	Total Gate Charge	V _{DS} = 80 V, I _D = 55 A,		75	98	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V (Note 4)		13		nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current				55	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				220	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 55 A			1.5	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V, } I_{S} = 55 \text{ A,}$		100		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		380	//	nC

- 1. Repetitive rating : pulse-width limited by maximum junction temperature.
- 2. L = 0.55 mH, I_{AS} = 55 A, V_{DD} = 25 V, R_G = 25 Ω , starting T_J = 25°C. 3. I_{SD} \leq 55 A, di/dt \leq 300 A/µs , V_{DD} \leq BV_{DSS}, starting T_J = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

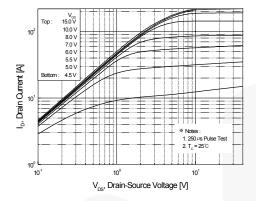


Figure 1. On-Region Characteristics

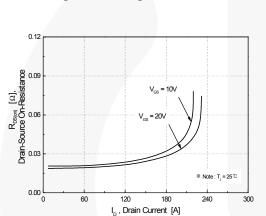


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

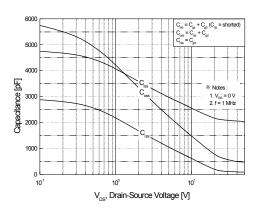


Figure 5. Capacitance Characteristics

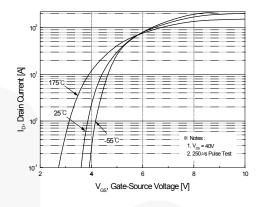


Figure 2. Transfer Characteristics

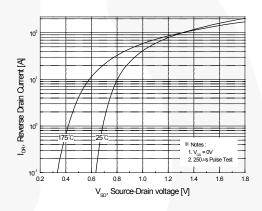


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

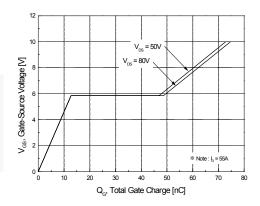


Figure 6. Gate Charge Characteristics

12 (Numaiized) BV₀₈₅, (Numaiized) BY₀₈₇, (Numaiized) BY₀₈₇

Typical Characteristics (Continued)

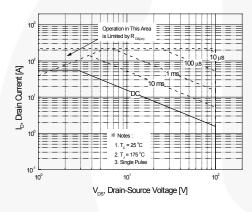
3.0 2.5 (Nowaligage) 1.5 (Nowaligage) 1.

Figure 7. Breakdown Voltage Variation vs. Temperature

T_J, Junction Temperature [°C]

150

Figure 8. On-Resistance Variation vs. Temperature



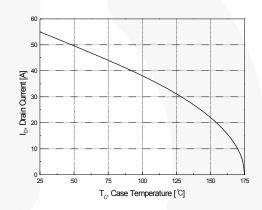


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

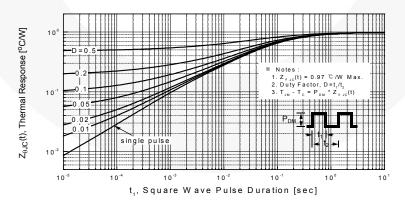


Figure 11. Transient Thermal Response Curve

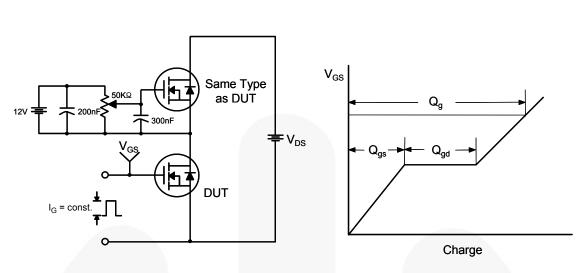


Figure 12. Gate Charge Test Circuit & Waveform

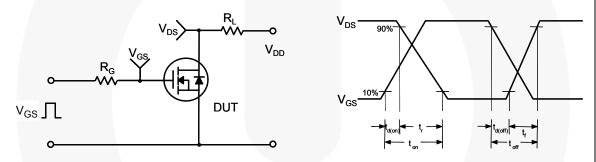


Figure 13. Resistive Switching Test Circuit & Waveforms

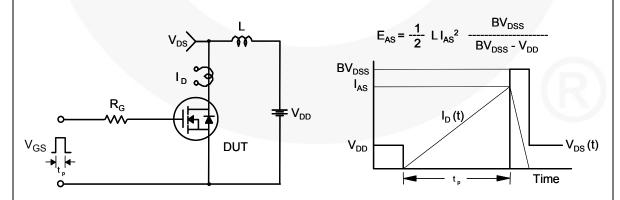
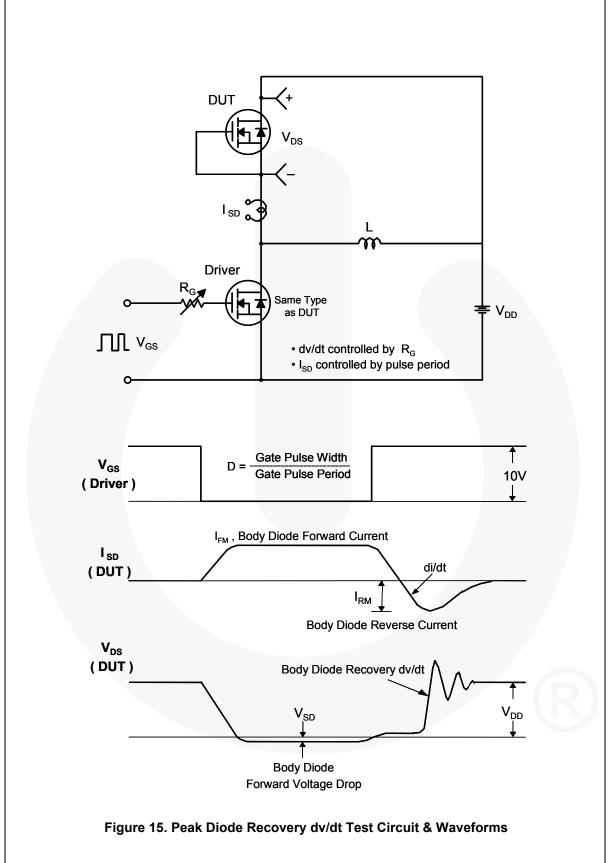


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

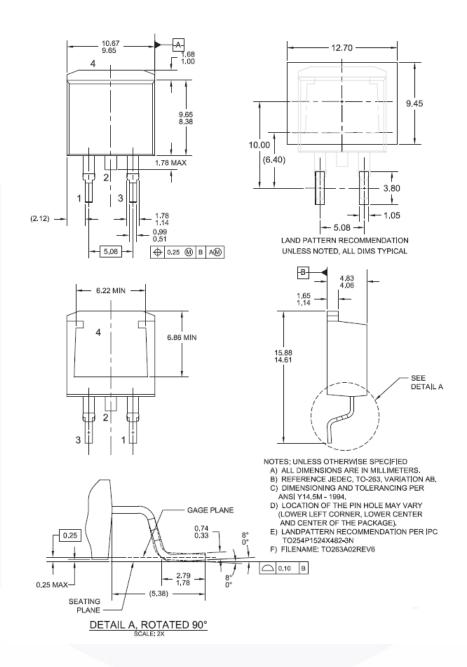


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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